



(19)

08109043 A

(11) Publication number:

Generated Document.

PATENT ABSTRACTS OF JAPAN

(21) Application number: 06266174

(51) Intl. Cl.: C03C 17/34 C03C 17/25 G06F 3/033 H01B 5/14

(22) Application date: 05.10.94

(30) Priority:

(43) Date of application publication: 30.04.96

(84) Designated contracting states:

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(54) TRANSPARENT
ELECTROCONDUCTIVE
FILM-ATTACHED GLASS
HAVING HIGH RESISTANCE

(57) Abstract:

PURPOSE: To obtain transparent electroconductive film-attached glass having high resistance and excellent in uniformity by forming a film of silicon dioxide onto a glass substrate and forming a transparent electroconductive film thereon to provide a film having two layer

structure.

CONSTITUTION: Silicon dioxide film containing phosphorus in an amount of 0.01-10wt.% and/or boron in an amount of 0.01-10wt.% based on silicon dioxide is formed on a transparent glass substrate in a film thickness of 60-150nm. A transparent electroconductive film having 1.7-2.2 refractive index, 200-3000 Ω /square and \pm 2% linearity value is formed in a film thickness of 10-30nm thereon to provide the objective transparent electroconductive film attached glass. ITO, FTO, ATO, etc., is used as the transparent electroconductive film and silicon dioxide is formed into a film by a sputtering method, a CVD method, a spraying method, etc.

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